

MOSFET

Metal Oxide Semiconductor Field Effect Transistor

OptiMOS™

OptiMOS™ 3 Power-Transistor, 40 V
IPA041N04N G

Data Sheet

Rev. 2.0
Final

1 Description

Features

- Optimized technology for DC/DC converters
- Qualified according to JEDEC ¹⁾ for target applications
- N-channel, normal level
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- Very low on-resistance $R_{DS(on)}$
- 100% Avalanche tested
- Pb-free plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

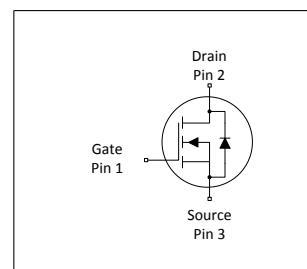


Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	40	V
$R_{DS(on),max}$	4.1	mΩ
I_D	70	A

Type / Ordering Code	Package	Marking	Related Links
IPA041N04N G	PG-TO220-FP	041N04N	-

¹⁾ J-STD20 and JESD22

Table of Contents

Description	2
Maximum ratings	4
Thermal characteristics	4
Electrical characteristics	5
Electrical characteristics diagrams	7
Package Outlines	11
Revision History	12
Disclaimer	12

2 Maximum ratings

at $T_j = 25\text{ °C}$, unless otherwise specified

Table 2 Maximum ratings
at 25 °C

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current	I_D	-	-	70 49	A	$V_{GS}=10\text{ V}$, $T_C=25\text{ °C}$ $V_{GS}=10\text{ V}$, $T_C=100\text{ °C}$
Pulsed drain current ¹⁾	$I_{D,pulse}$	-	-	280	A	$T_C=25\text{ °C}$
Avalanche current, single pulse ²⁾	I_{AS}	-	-	70	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse	E_{AS}	-	-	70	mJ	$I_D=70\text{ A}$, $R_{GS}=25\text{ }\Omega$
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	35	W	$T_C=25\text{ °C}$
Operating and storage temperature	T_j, T_{stg}	-55	-	175	°C	IEC climatic category; DIN IEC 68-1: 55/175/56

3 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	4.3	K/W	-
SMD version, device on PCB, minimal footprint	R_{thJA}	-	-	62	K/W	-
SMD version, device on PCB, 6 cm ² cooling area ³⁾	R_{thJA}	-	-	40	K/W	-

¹⁾ See figure 3 for more detailed information

²⁾ See figure 13 for more detailed information

³⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

4 Electrical characteristics

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	40	-	-	V	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	2	-	4	V	$V_{DS}=V_{GS}$, $I_D=45\text{ }\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	0.1 10	1 100	μA	$V_{DS}=40\text{ V}$, $V_{GS}=0\text{ V}$, $T_J=25\text{ }^\circ\text{C}$ $V_{DS}=40\text{ V}$, $V_{GS}=0\text{ V}$, $T_J=125\text{ }^\circ\text{C}$
Gate-source leakage current	I_{GSS}	-	10	100	nA	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance ¹⁾	$R_{DS(on)}$	-	3.5	4.1	m Ω	$V_{GS}=10\text{ V}$, $I_D=70\text{ A}$
Gate resistance	R_G	-	1.6	2.4	Ω	-
Transconductance	g_{fs}	48	96	-	S	$ V_{DS} >2 I_D /R_{DS(on)max}$, $I_D=70\text{ A}$

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	3400	4500	pF	$V_{GS}=0\text{ V}$, $V_{DS}=20\text{ V}$, $f=1\text{ MHz}$
Output capacitance	C_{oss}	-	980	1300	pF	$V_{GS}=0\text{ V}$, $V_{DS}=20\text{ V}$, $f=1\text{ MHz}$
Reverse transfer capacitance	C_{rss}	-	36	72	pF	$V_{GS}=0\text{ V}$, $V_{DS}=20\text{ V}$, $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	16	-	ns	$V_{DD}=20\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=30\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Rise time	t_r	-	3.8	-	ns	$V_{DD}=20\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=30\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	-	23	-	ns	$V_{DD}=20\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=30\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Fall time	t_f	-	4.8	-	ns	$V_{DD}=20\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=30\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$

Table 6 Gate charge characteristics ²⁾

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	18	-	nC	$V_{DD}=20\text{ V}$, $I_D=30\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge at threshold	$Q_{g(th)}$	-	10.3	-	nC	$V_{DD}=20\text{ V}$, $I_D=30\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge	Q_{gd}	-	5.3	-	nC	$V_{DD}=20\text{ V}$, $I_D=30\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Switching charge	Q_{sw}	-	12.5	-	nC	$V_{DD}=20\text{ V}$, $I_D=30\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total	Q_g	-	42	56	nC	$V_{DD}=20\text{ V}$, $I_D=30\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	5.1	-	V	$V_{DD}=20\text{ V}$, $I_D=30\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total, sync. FET	$Q_{g(sync)}$	-	40	-	nC	$V_{DS}=0.1\text{ V}$, $V_{GS}=0\text{ to }10\text{ V}$
Output charge	Q_{oss}	-	41	-	nC	$V_{DD}=20\text{ V}$, $V_{GS}=0\text{ V}$

¹⁾ Measured from drain tab to source pin

²⁾ See "Gate charge waveforms" for parameter definition

Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	29	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	280	A	$T_C=25\text{ °C}$
Diode forward voltage	V_{SD}	-	0.87	1.2	V	$V_{GS}=0\text{ V}$, $I_F=29\text{ A}$, $T_J=25\text{ °C}$
Reverse recovery charge	Q_{rr}	-	19	-	nC	$V_R=20\text{ V}$, $I_F=29\text{ A}$, $di_F/dt=400\text{ A}/\mu\text{s}$

5 Electrical characteristics diagrams

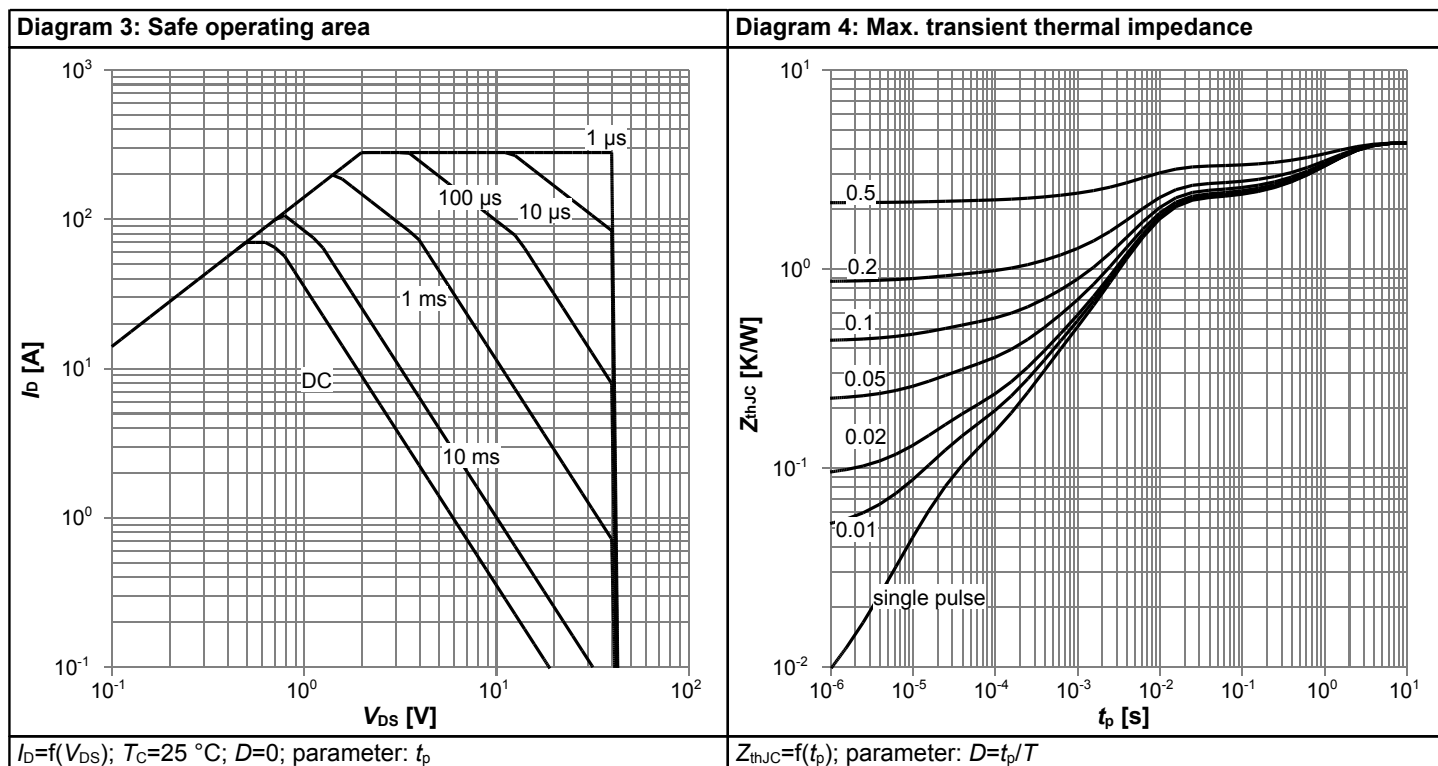
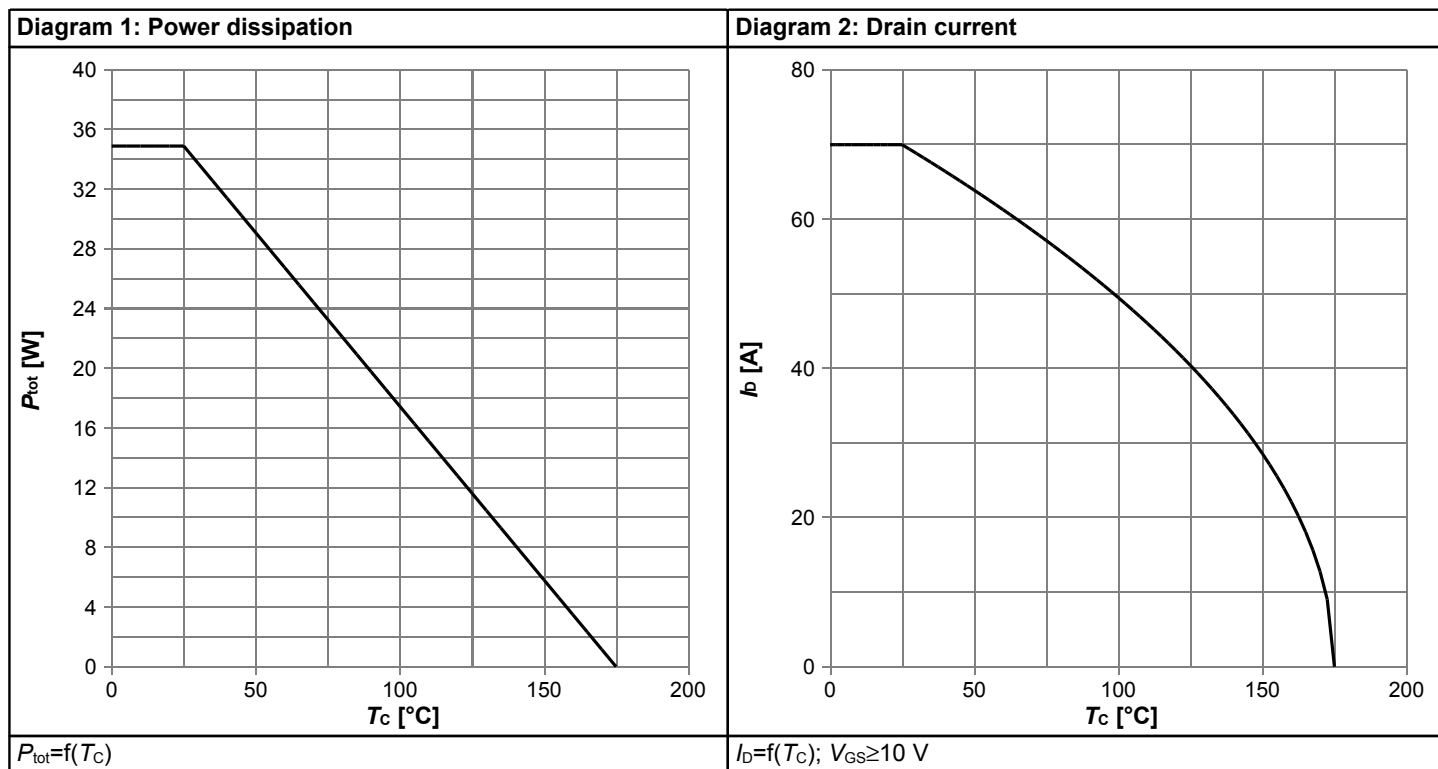


Diagram 5: Typ. output characteristics

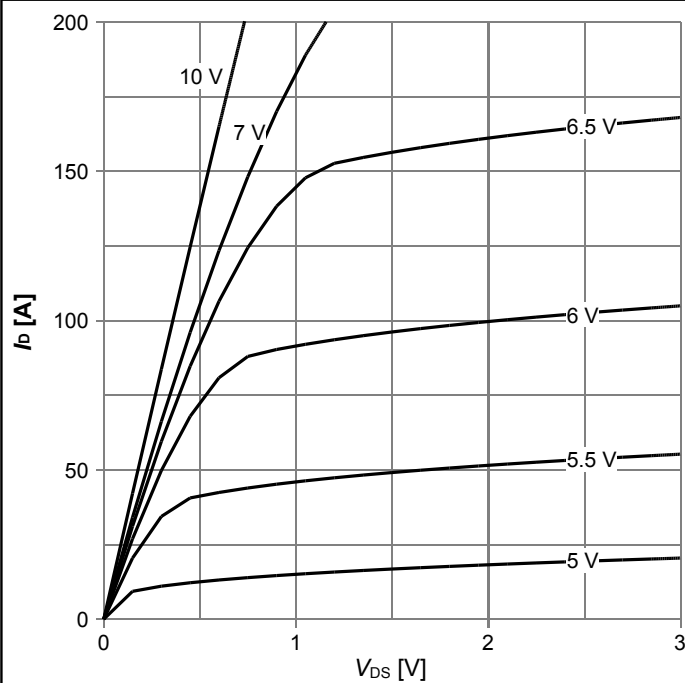

 $I_D = f(V_{DS}); T_j = 25^\circ\text{C}; \text{parameter: } V_{GS}$

Diagram 6: Typ. drain-source on resistance

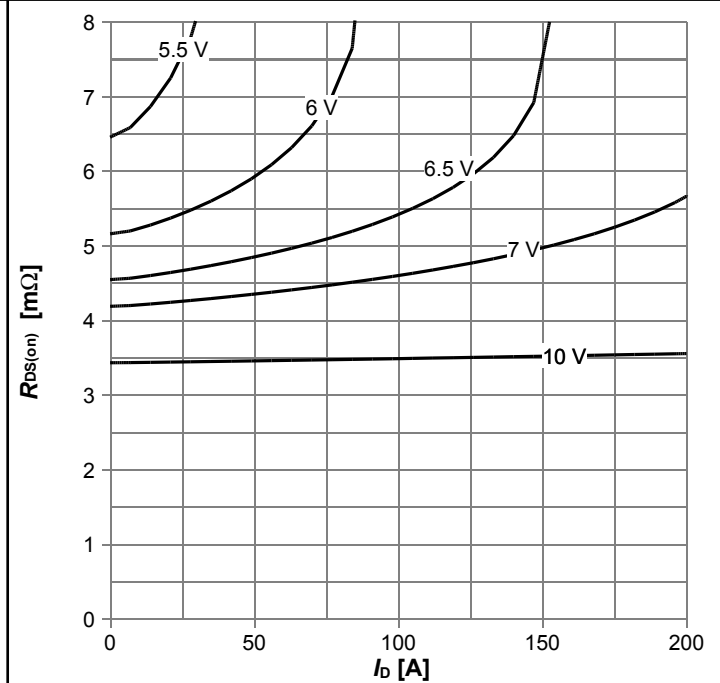

 $R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}; \text{parameter: } V_{GS}$

Diagram 7: Typ. transfer characteristics

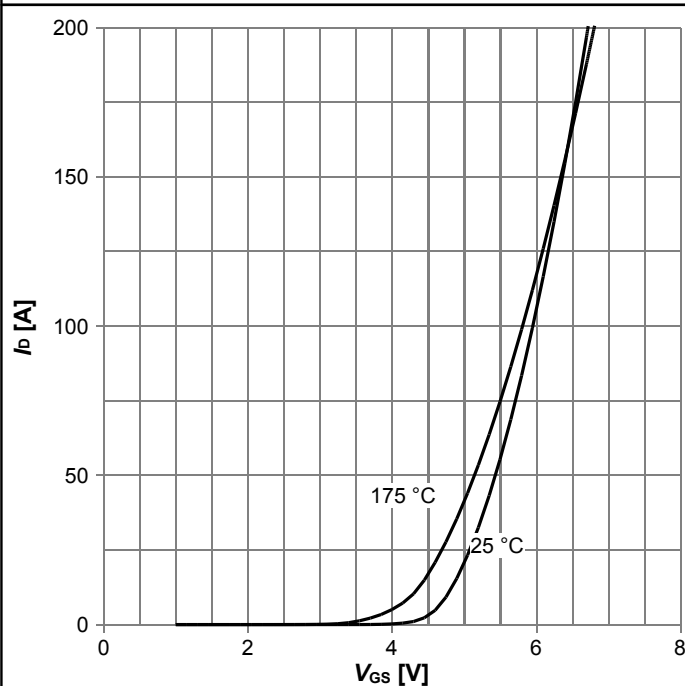

 $I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}; \text{parameter: } T_j$

Diagram 8: Typ. forward transconductance

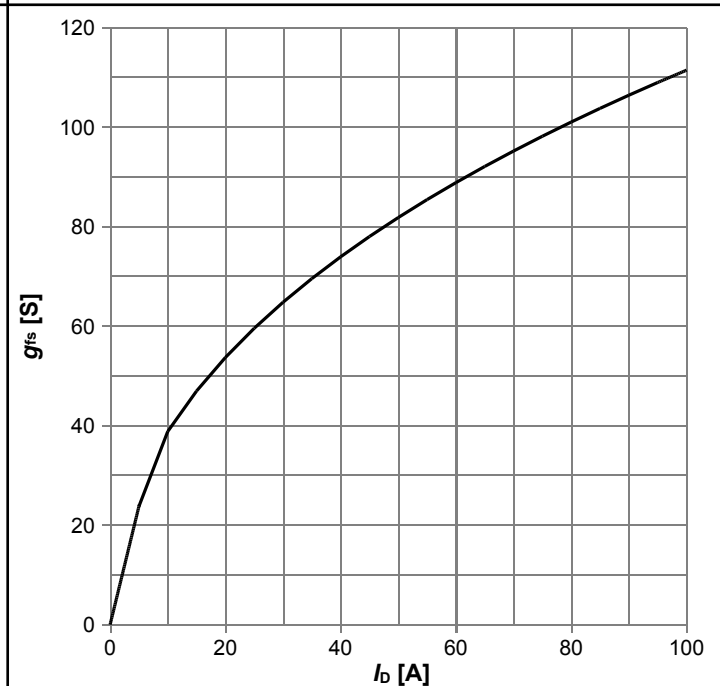
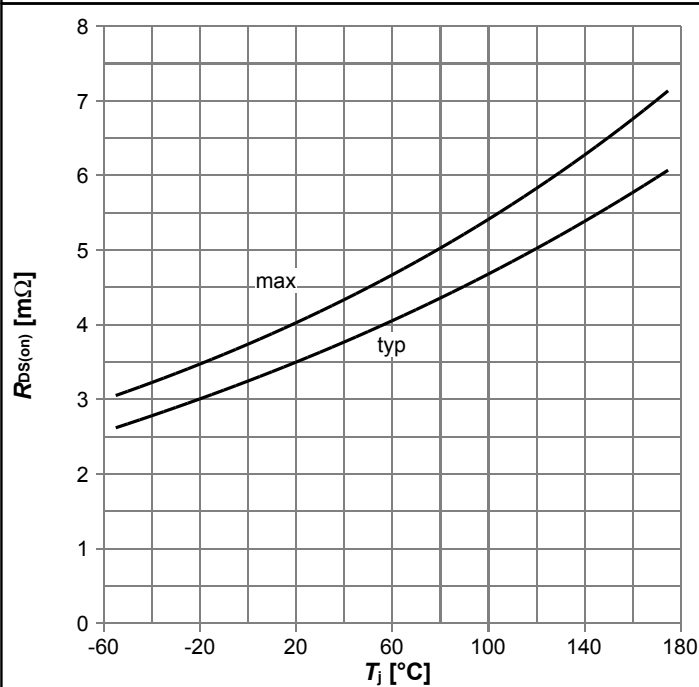
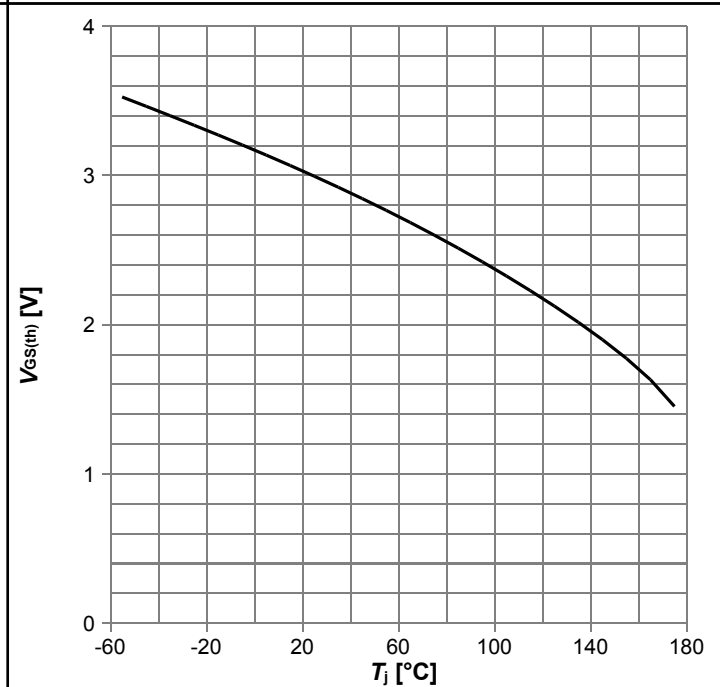

 $g_{fs} = f(I_D); T_j = 25^\circ\text{C}$

Diagram 9: Drain-source on-state resistance



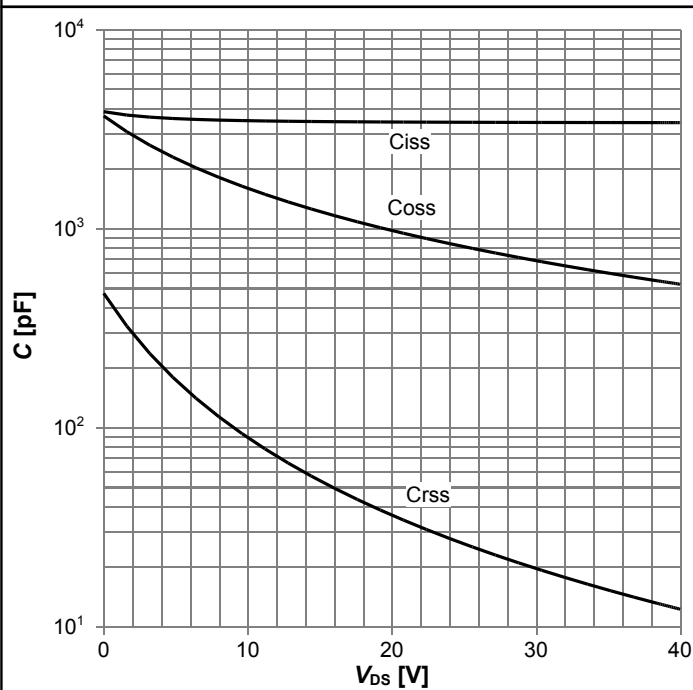
$$R_{DS(on)} = f(T_j); I_D = 70 \text{ A}; V_{GS} = 10 \text{ V}$$

Diagram 10: Typ. gate threshold voltage



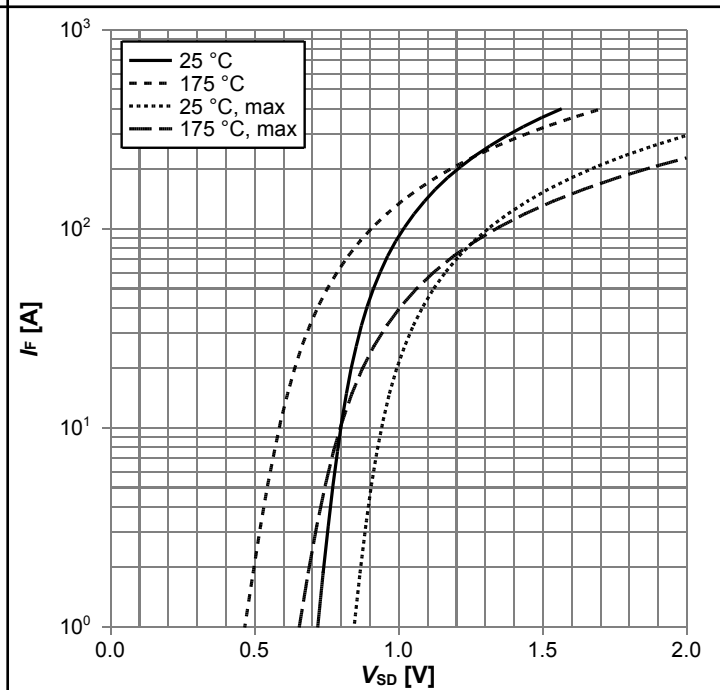
$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}; I_D = 45 \text{ μA}$$

Diagram 11: Typ. capacitances



$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$

Diagram 12: Forward characteristics of reverse diode



$$I_F = f(V_{SD}); \text{parameter: } T_j$$

Diagram 13: Avalanche characteristics

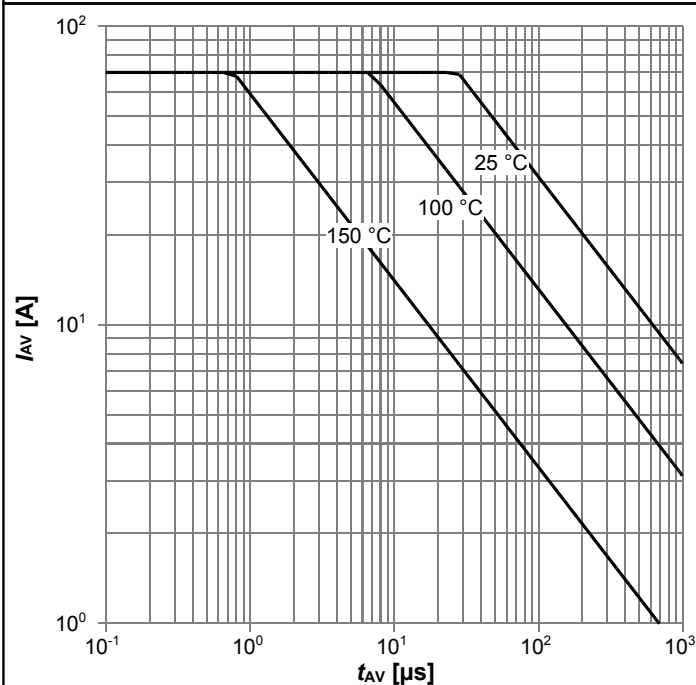

 $I_{AS}=f(t_{AV}); R_{GS}=25\ \Omega; \text{parameter: } T_{j(\text{start})}$

Diagram 14: Typ. gate charge

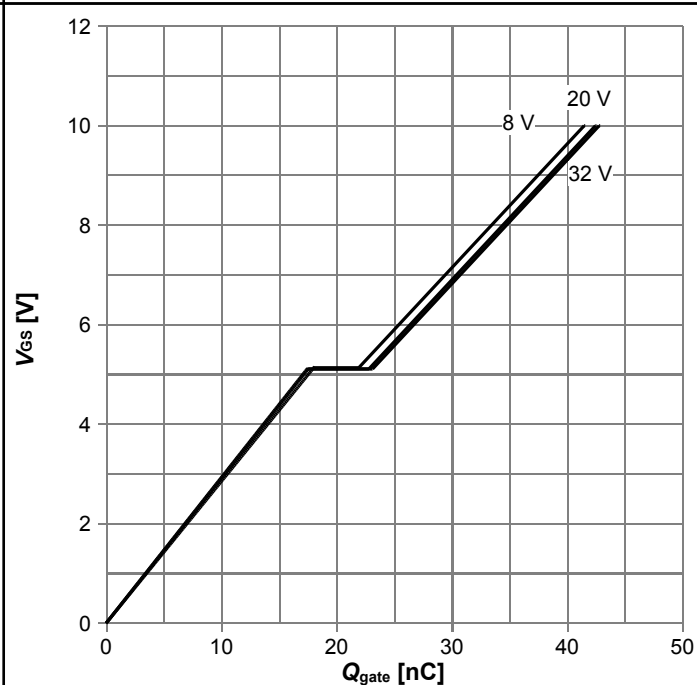
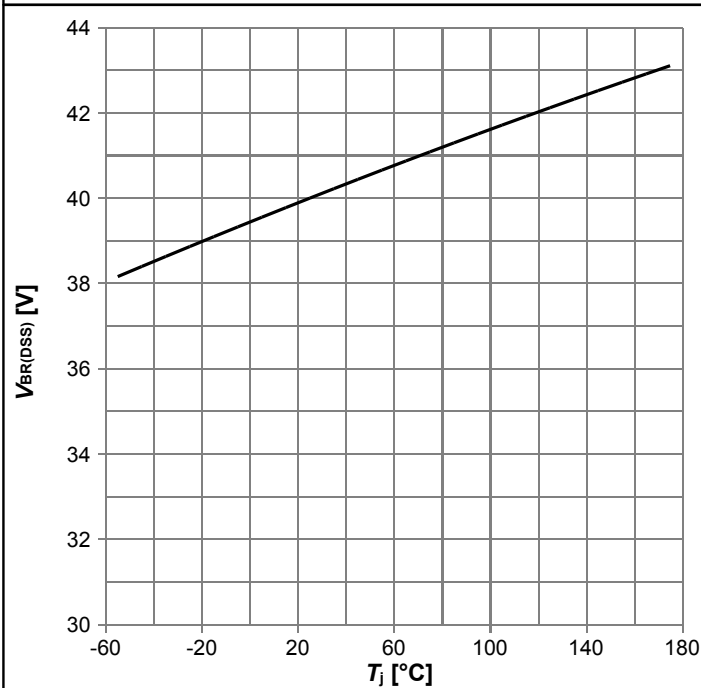
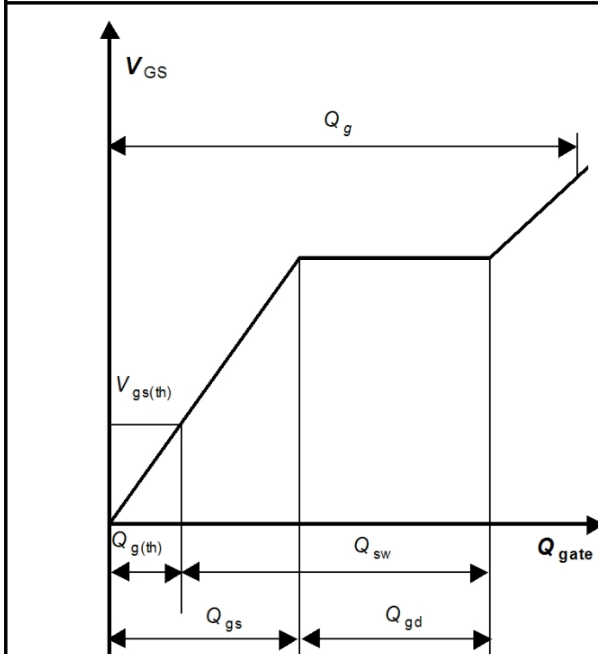

 $V_{GS}=f(Q_{\text{gate}}); I_D=30\ \text{A pulsed}; \text{parameter: } V_{DD}$

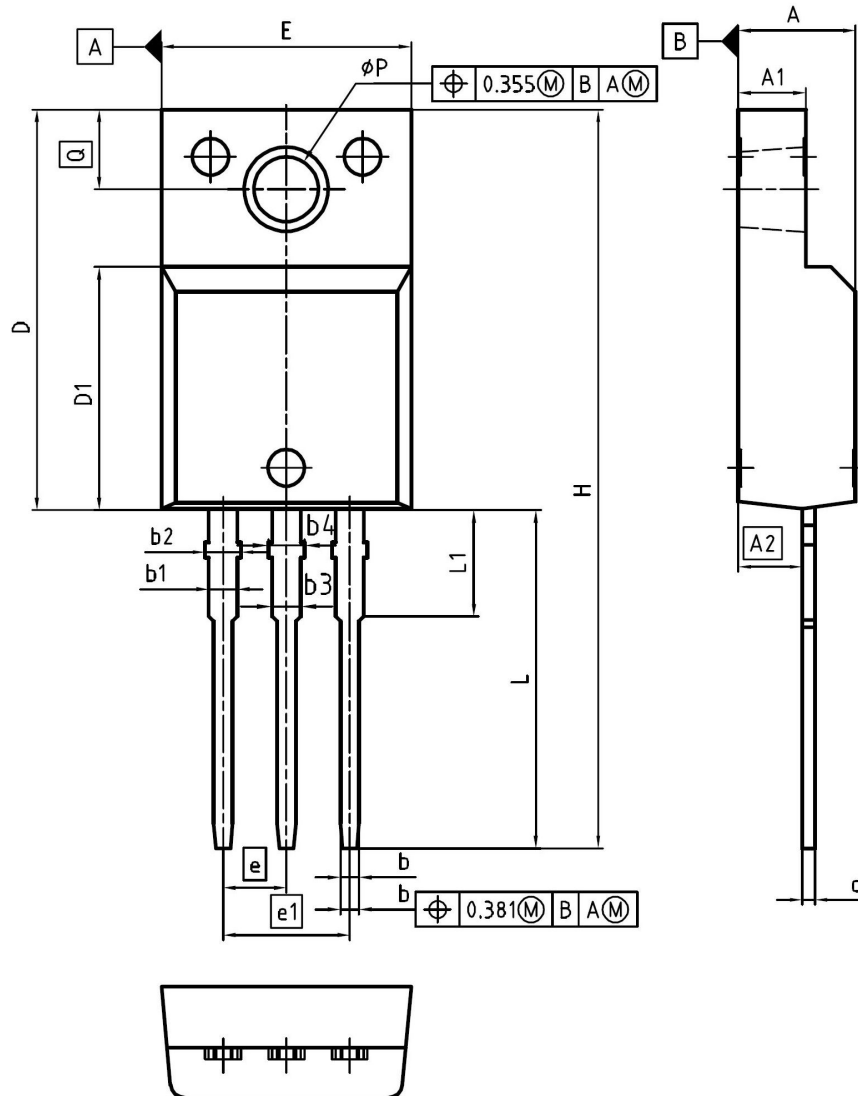
Diagram 15: Drain-source breakdown voltage


 $V_{BR(DSS)}=f(T_j); I_D=1\ \text{mA}$

Gate charge waveforms



6 Package Outlines



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.55	4.85	0.179	0.191
A1	2.55	2.85	0.100	0.112
A2	2.42	2.72	0.095	0.107
b	0.65	0.85	0.026	0.033
b1	0.95	1.33	0.037	0.052
b2	0.95	1.51	0.037	0.059
b3	0.65	1.33	0.026	0.052
b4	0.65	1.51	0.026	0.059
c	0.40	0.63	0.016	0.025
D	15.85	16.15	0.624	0.636
D1	9.53	9.83	0.375	0.387
E	10.35	10.65	0.407	0.419
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H	29.45	29.75	1.159	1.171
L	13.45	13.75	0.530	0.541
L1	3.15	3.45	0.124	0.136
øP	2.95	3.20	0.116	0.126
Q	3.15	3.50	0.124	0.138

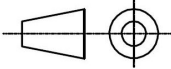
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SCALE 0 2.5 5mm
EUROPEAN PROJECTION 
ISSUE DATE 08-03-2007
REVISION 03

Figure 1 Outline PG-TO220-FP, dimensions in mm/inches

Revision History

IPA041N04N G

Revision: 2014-03-12, Rev. 2.0

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2014-03-12	Release of final version

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Infineon Technologies AG

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